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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/767,357	01/28/2004	Tito Gelsomini	TI-36896	4880
23494 7	7590 08/17/2006		EXAMINER	
TEXAS INSTRUMENTS INCORPORATED			ROSASCO, STEPHEN D	
P O BOX 655474, M/S 3999 DALLAS, TX 75265			ART UNIT	PAPER NUMBER
,			1756	
			DATE MAILED: 08/17/2006	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
Office Action Summary	10/767,357	GELSOMINI, TITO				
Office Action Summary	Examiner	Art Unit				
The MAILING DATE of this communication and	Stephen Rosasco	1756				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period w  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tirr vill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	I.  lety filed  the mailing date of this communication.  D (35 U.S.C. § 133).				
Status						
1)⊠ Responsive to communication(s) filed on 25 Ju	ne 2004.					
2a) ☐ This action is <b>FINAL</b> . 2b) ☒ This	☐ This action is <b>FINAL</b> . 2b) ☑ This action is non-final.					
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 45	33 O.G. 213.				
Disposition of Claims						
4) ☐ Claim(s) 1 and 2 is/are pending in the application 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1 and 2 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	vn from consideration.					
Application Papers						
9) ☐ The specification is objected to by the Examiner 10) ☑ The drawing(s) filed on 25 June 2004 is/are: a)  Applicant may not request that any objection to the ore Replacement drawing sheet(s) including the correction 11) ☐ The oath or declaration is objected to by the Examiner 11.	☑ accepted or b)☐ objected to drawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).				
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Application ity documents have been receive (PCT Rule 17.2(a)).	on No ed in this National Stage				
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:					

## **Detailed Action**

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1-2 are rejected under 35 U.S.C. 102(b) as being clearly anticipated by Tsai et al. (6,413,685).

Tsai et al. teach (see claims) a method of reducing the optical proximity effect of an exposed etch pattern occurred during a conventional photolithography process, wherein a primary pattern according to the present invention is first divided into a plurality of subpatterns. Each of the sub-patterns formed on a photomask is then exposed under a light source to be sequentially transferred onto a corresponding photoresist layer during a photolithography process. Subsequently, the operating parameters of a stepper used in the photolithography process such as numerical perture, coherence, intensity of energy, and intensity of light are set according to the charts as shown in FIG. 5A, 5B, 6A, 6B, and 6C to obtain desirable critical dimensions, thereby reduces the optical proximity effect.

Therefore, an etch pattern with different line pitches can be successfully transferred onto a photoresist layer with each critical dimension of the different line pitches accurately met according to the present invention.

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Claims 1-2 are rejected under 35 U.S.C. 102(e) as being anticipated by Magome et al. (6,677,088) or Dirksen et al. (7,037,626).

Magome et al. teach (see claims 12+) a method of manufacturing a device in which a circuit pattern is formed on an object, comprising: providing plural segmented patterns, in which a

Dirksen et al. teach (see claims) a method for lithographically manufacturing a device with a very high density, a design mask pattern is distributed on a number of subpatterns. The sub-patterns do not comprise "forbidden" structures and can be transferred by conventional apparatus to a substrate layer to be patterned.

## Conclusion

Any inquiry concerning this communication or earlier communications from the Examiner should be directed to Stephen Rosasco whose telephone number is (571) 272-1389. The Examiner can normally be reached Monday-Friday, from 8:00 AM to 4:30 PM. The Examiner's supervisor, Mark Huff, can be reached on (571) 272-1385. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

S. Rosasco

Primary Examiner

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S.Rosasco 08/09/06